

1250-DDF Major components

Vacuum system		
Vacuum chamber volume with rotating substrate holder	1940 l	
Preliminary vacuum pumps (rotary + roots pump)	280 m ³ /h	2050 m ³ /h
Diffusion pump	15'000 l/s	
Baffle	630 mm dia	
Meissner trap (water vapour pumping speed)	160'000 l/s	
End vacuum after 24 hours outgassing at 300°C	1 E – 4 Pa	
Electron beam evaporation system		
Emission current	0.6 A max.	
High voltage output	10 kV max.	
Crucible diameter	133 mm	
Beam deflection	270°C	
Quartz film thickness measuring unit		
Quartz measuring head	1	
Frequency	6 MHz	
Thermal evaporation unit (optional)		
Number of thermal sources	2 max.	
Rated maximum power	3 kVA each	
Plasma rod (optional)		
Voltage (output)	1500 V typical	
Emission current	250 mA typical	
Substrate heating systems available (depending on process)		
Bottom heater	maximum temperature 150°C	
Top heater	maximum temperature 300°C	
Substrate holders systems available		
Lens holder drum	external diameter 1035 mm	
Process control system		
S-9380	Windows-based operator menus Touch screen monitor for different interface levels Full automatic plant control Data logging for process and service Remote control for real-time support	
Standard accessory		
NA-9 Water thermo conditioner	Included (see separate data sheet)	